



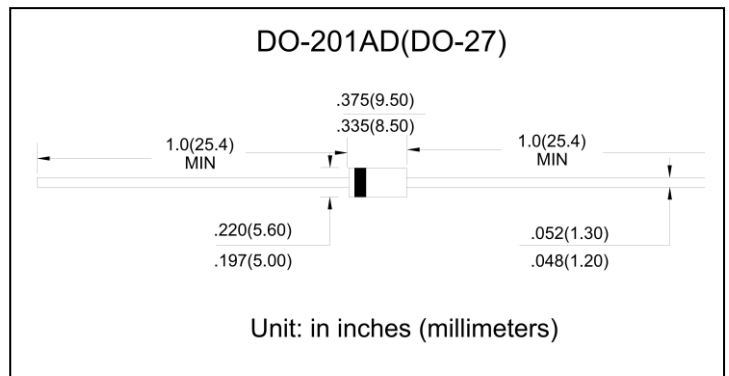
**SR3A100L Schottky Barrier Diode**

**Feature**

- High current capability
- Low VF, Low IR
- High Junction Temperature
- High surge current capability

**Application**

- Rectifier



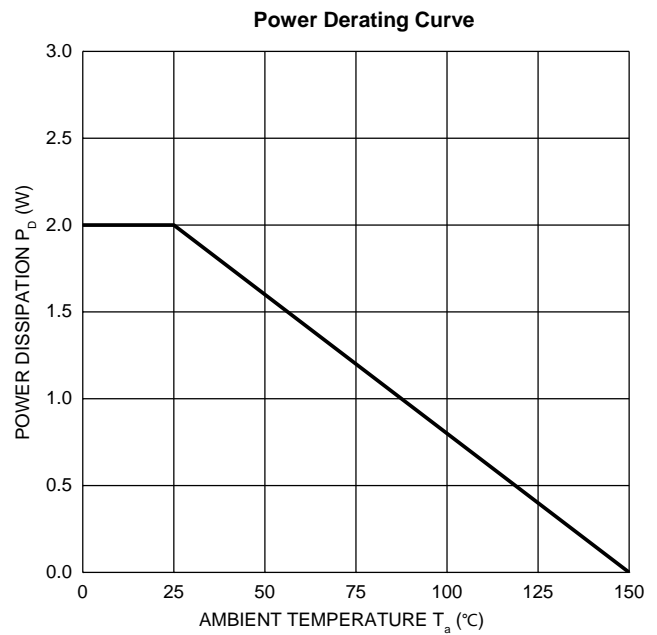
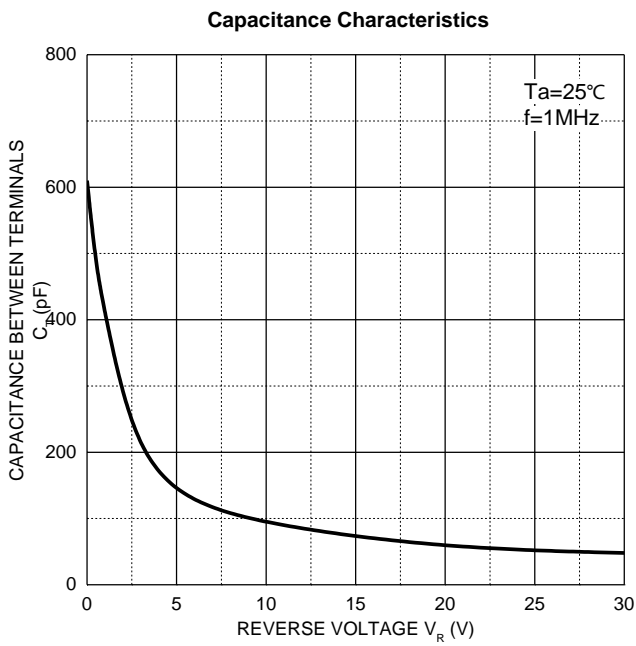
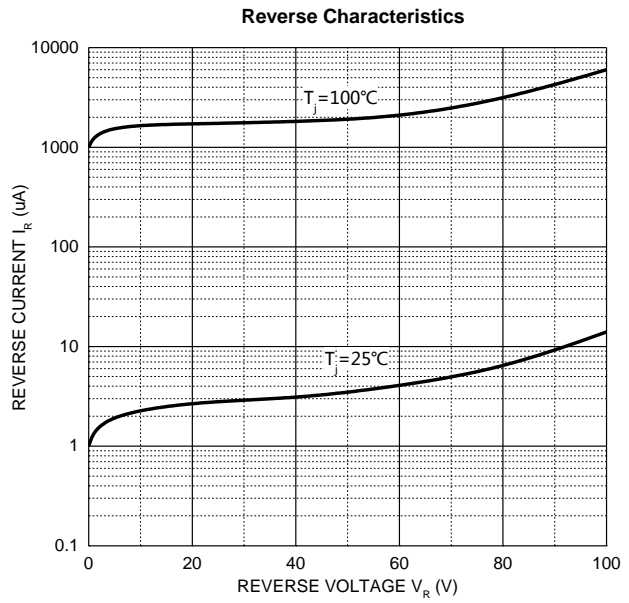
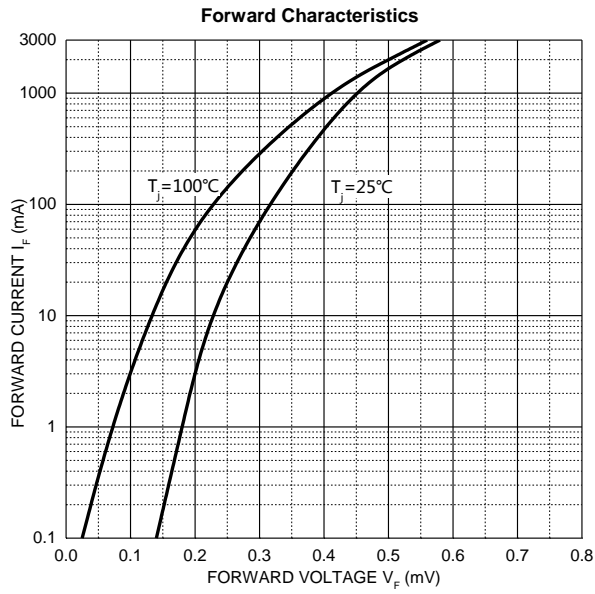
**ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	100	V
Maximum RMS Voltage	V <sub>RSM</sub>	70	V
Maximum DC blocking Voltage	V <sub>DC</sub>	100	V
Mean rectifying current	I <sub>o</sub>	3.0	A
Non-repetitive Peak Forward Surge Current @ t=8.3ms	I <sub>FSM</sub>	80	A
Maximum Junction Temperature	T <sub>J</sub>	125	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

**ELECTRICAL CHARACTERISTICS(T<sub>a</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Typical	Max	Unit
Reverse voltage	V <sub>BR</sub>	I <sub>R</sub> =250μA	100	110		V
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =1A		0.45	0.49	V
		I <sub>F</sub> =2A		0.52	0.56	V
		I <sub>F</sub> =3A		0.58	0.62	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =100V		20	100	μA
Typical Thermal Resistance	R <sub>θJ-A</sub>	Between junction and ambient	40			°C/W
	R <sub>θJ-L</sub>	Between junction and lead	10			°C/W
Typical Junction Capacitance	C <sub>J</sub>	V <sub>R</sub> =4V, f=1MHz	200			pF

**Typical Characteristics**



单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)